Product data sheet

1. General description

P-channel enhancement mode Field-Effect Transistor (FET) in a medium power SOT223 (SC-73) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

2. Features and benefits

- · Logic level compatible
- · Very fast switching
- Trench MOSFET technology
- ElectroStatic Discharge (ESD) protection > 2 kV HBM

3. Applications

- · Relay driver
- · High-speed line driver
- · High-side loadswitch
- · Switching circuits

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit	
V_{DS}	drain-source voltage	T _j = 25 °C		-	-	-70	V	
V_{GS}	gate-source voltage			-20	-	20	V	
I _D	drain current	V_{GS} = -10 V; T_{amb} = 25 °C	[1]	-	-	-2.4	Α	
Static characte	Static characteristics							
R _{DSon}	drain-source on-state resistance	V_{GS} = -10 V; I_D = -2.4 A; T_j = 25 °C		-	130	167	mΩ	

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm².



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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	4	D
2	D	drain		
3	S	source		G \downarrow \downarrow \downarrow
4	D	drain	⊟1 ⊟2 ⊟3 SC-73 (SOT223)	S 017aaa259

6. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
PMT200EPE	SC-73	plastic surface-mounted package with increased heatsink; 4 leads	SOT223			

7. Marking

Table 4. Marking codes

Type number	Marking code
PMT200EPE	T2EPE

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8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{DS}	drain-source voltage	T _j = 25 °C		-	-70	V
V _{GS}	gate-source voltage			-20	20	V
I _D	drain current	V _{GS} = -10 V; T _{amb} = 25 °C	[1]	-	-2.4	Α
		V _{GS} = -10 V; T _{amb} = 100 °C	[1]	-	-1.5	Α
I _{DM}	peak drain current	T_{amb} = 25 °C; single pulse; $t_p \le 10 \mu s$		-	-9.7	Α
P _{tot}	total power dissipation	T _{amb} = 25 °C	[2]	-	800	mW
			[1]	-	1.75	W
		T _{sp} = 25 °C		-	8.3	W
T _j	junction temperature			-55	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C
E _{DS(AL)S}	non-repetitive drain- source avalanche energy	$T_{j(init)}$ = 25 °C; I_D = -1.3 A; DUT in avalanche (unclamped)		-	19.5	mJ
Source-drain d	liode					,
Is	source current	T _{amb} = 25 °C	[1]	-	-1.8	Α
ESD maximum	rating		'	,		
V _{ESD}	electrostatic discharge voltage	НВМ	[3]	-	2000	V

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm².

^[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

^[3] Measured between all pins.

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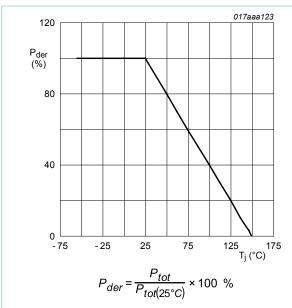


Fig. 1. Normalized total power dissipation as a function of junction temperature

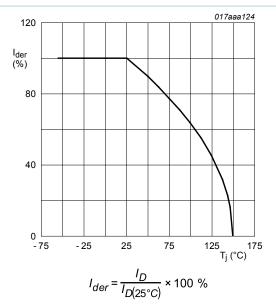


Fig. 2. Normalized continuous drain current as a function of junction temperature

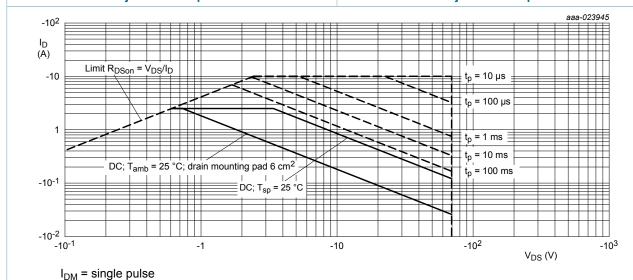


Fig. 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

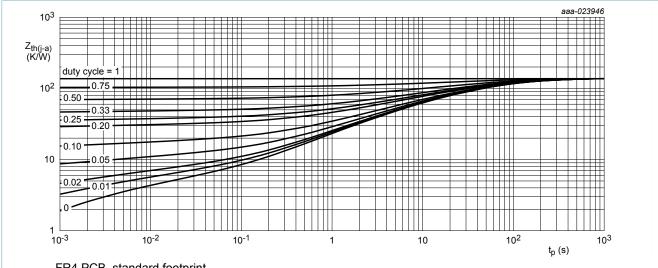
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9. Thermal characteristics

Table 6. Thermal characteristics

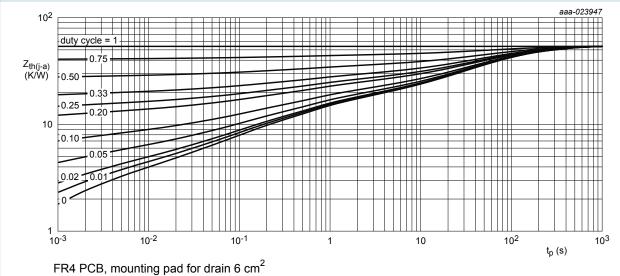
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-a)}	thermal resistance from junction to ambient		[1]	-	135	155	K/W
			[2]	-	54	70	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	7	15	K/W

- Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm².



FR4 PCB, standard footprint

Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



Transient thermal impedance from junction to ambient as a function of pulse duration; typical values Fig. 5.

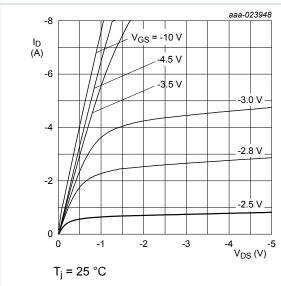
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10. Characteristics

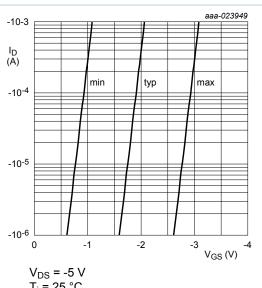
Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					,
V _{(BR)DSS}	drain-source breakdown voltage	I_D = -250 μ A; V_{GS} = 0 V; T_j = 25 °C	-70	-	-	V
V_{GSth}	gate-source threshold voltage	I_D = -250 μ A; V_{DS} = V_{GS} ; T_j = 25 °C	-1	-2	-3	V
I _{DSS}	drain leakage current	V _{DS} = -70 V; V _{GS} = 0 V; T _j = 25 °C	-	-	-1	μA
I _{GSS}	gate leakage current	V _{GS} = 20 V; V _{DS} = 0 V; T _j = 25 °C	-	-	10	μA
		V _{GS} = -20 V; V _{DS} = 0 V; T _j = 25 °C	-	-	-10	μA
		V _{GS} = 10 V; V _{DS} = 0 V; T _j = 25 °C	-	-	2	μA
		V _{GS} = -10 V; V _{DS} = 0 V; T _j = 25 °C	-	-	-2	μA
R _{DSon}	drain-source on-state	V_{GS} = -10 V; I_D = -2.4 A; T_j = 25 °C	-	130	167	mΩ
	resistance	V _{GS} = -10 V; I _D = -2.4 A; T _j = 150 °C	-	234	250	mΩ
		V_{GS} = -4.5 V; I_D = -2.1 A; T_j = 25 °C	-	150	225	mΩ
g _{fs}	forward transconductance	V_{DS} = -10 V; I_D = -2.4 A; T_j = 25 °C	-	13.5	-	S
R_G	gate resistance	f = 1 MHz	-	12	-	Ω
Dynamic ch	naracteristics					
Q _{G(tot)}	total gate charge	V_{DS} = -35 V; I_{D} = -2.4 A; V_{GS} = -10 V;	-	10.6	15.9	nC
Q _{GS}	gate-source charge	T _j = 25 °C	-	2.2	-	nC
Q _{GD}	gate-drain charge		-	1.05	-	nC
C _{iss}	input capacitance	V _{DS} = -35 V; f = 1 MHz; V _{GS} = 0 V;	-	822	-	pF
C _{oss}	output capacitance	T _j = 25 °C	-	47	-	pF
C _{rss}	reverse transfer capacitance		-	31.5	-	pF
t _{d(on)}	turn-on delay time	V_{DS} = -35 V; I_{D} = -2.4 A; V_{GS} = -10 V;	-	6	-	ns
t _r	rise time	$R_{G(ext)} = 6 \Omega$; $T_j = 25 °C$	-	8	-	ns
t _{d(off)}	turn-off delay time		-	42	-	ns
t _f	fall time		-	20	-	ns
Source-drai	in diode		1	,		,
V_{SD}	source-drain voltage	I _S = -2.4 A; V _{GS} = 0 V; T _i = 25 °C	-	-0.8	-1.2	V

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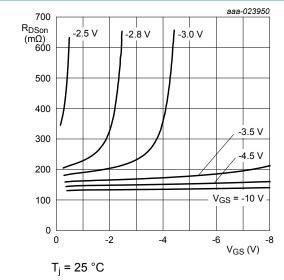


Output characteristics: drain current as a Fig. 6. function of drain-source voltage; typical values

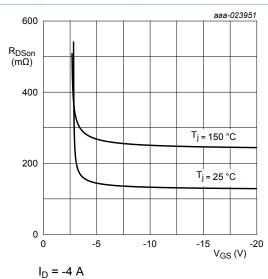


 V_{DS} = -5 V T_j = 25 $^{\circ}$ C

Sub-threshold drain current as a function of Fig. 7. gate-source voltage



Drain-source on-state resistance as a function Fig. 8. of drain current; typical values



Drain-source on-state resistance as a function Fig. 9. of gate-source voltage; typical values

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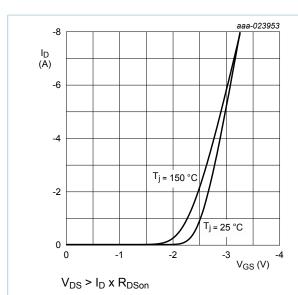


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

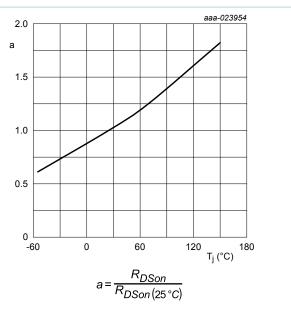


Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values

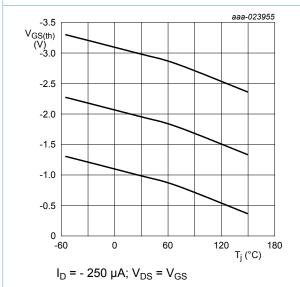


Fig. 12. Gate-source threshold voltage as a function of junction temperature

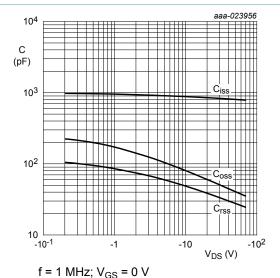
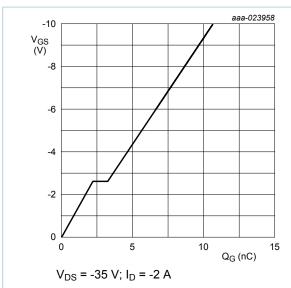


Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

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V_{DS}

V_{GS(pl)}

V_{GS(th)}

V_{GS}

Q_{GS1}

Q_{GS2}

Q_{GG1}

Q_{GS2}

Q_{G(tot)}

003aaa508

Fig. 15. Gate charge waveform definitions

Fig. 14. Gate-source voltage as a function of gate charge; typical values

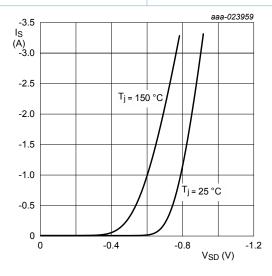
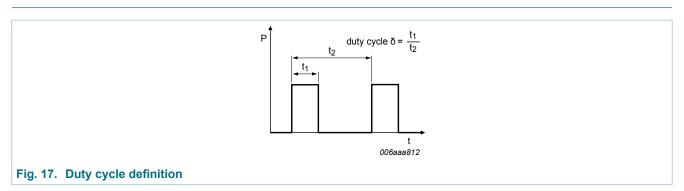


Fig. 16. Source current as a function of source-drain voltage; typical values

11. Test information

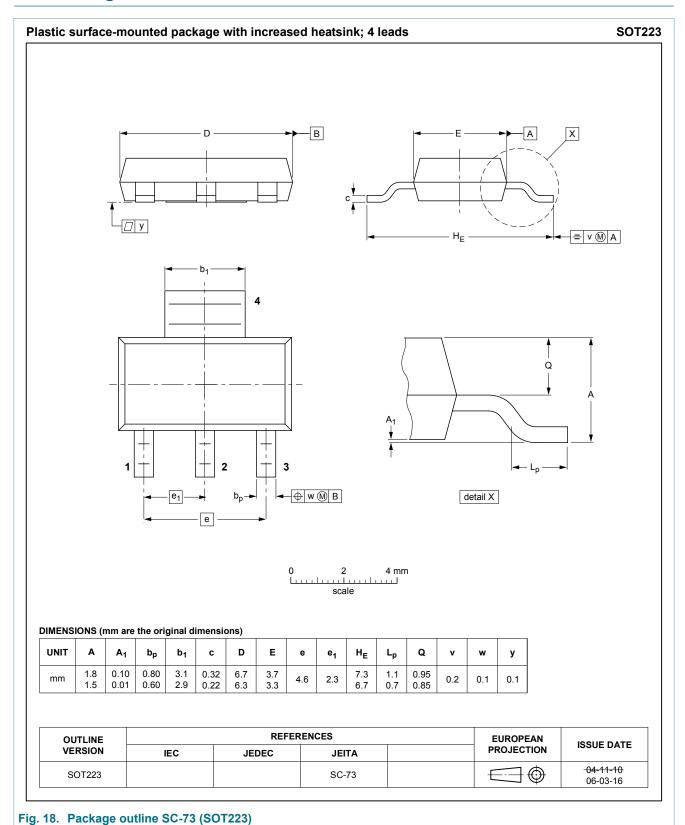
 $V_{GS} = 0 V$



PMT200EPE

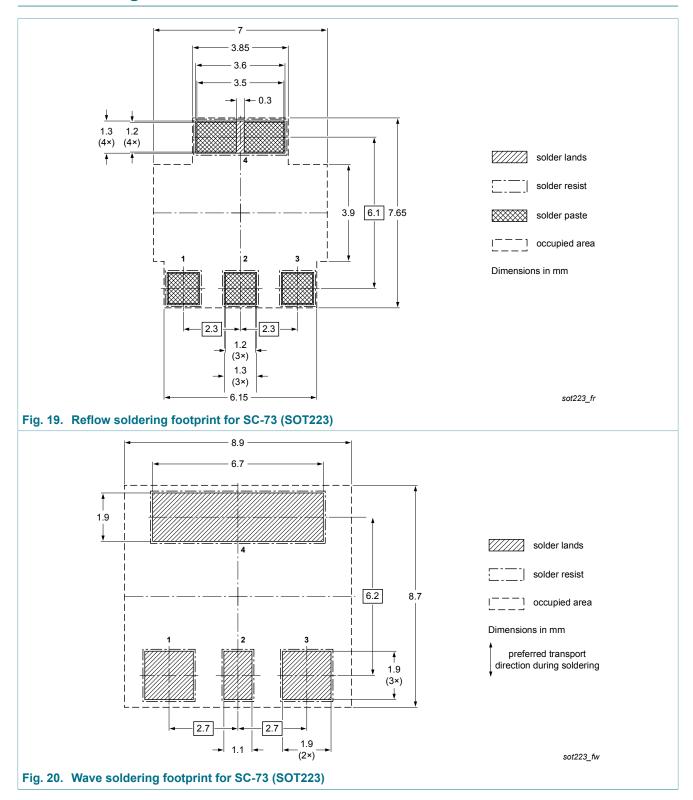
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12. Package outline



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13. Soldering



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14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PMT200EPE v.1	20180314	Product data sheet	-	-

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15. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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